FORM PTO-1449 U.S. Department of Commerce (Rev. 4/92)

EXAMINER

Patent and Trademark Office

ATTY, DOCKET NO. 501.22642CC9

SERIAL NO.

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use several sheets if necessary)

APPLICANT FUJISAKI et al

FILING DATE

GROUP

July 23, 2003 **U.S. PATENT DOCUMENTS** EXAMINER FILING DATE DOCUMENT NUMBER DATE NAME CLASS SUBCLASS 5 4 4 7 10/85 Clarke 1 Shimoda 3 10/86 4 6 1 8 9 6 8 3 3 3 4 2 9/74 3 Holliday 0 3 5/69 3 4 4 6 6 Loiacono 3 0 3 0 5/62 Okkerse 3 6 6 9 9 6 5 0 11/81 Bonner 2 9 0 8 0 0 4 10/59 Levinson 7 9/85 4 5 3 9 0 6 Washizuka 4 5 8 6 9 7 9 5/86 Katsumata 6 3 8 5 4 1/87 **Fukuda** 6 5 5 6 0 2/87 Matsumoto FOREIGN PATENT DOCUMENTS DOCUMENT NUMBER DATE COUNTRY CLASS SUBCLASS TRANSLATION YES NO: Х 9 9/80 55 3 6 9 Japan 1 OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) Ghandhi, S. VLSI Fabrication Principles, John Wiley, 1983 pp 86-90, 98-100 Sze, S., Physics of Semiconductor Devices, John Wiley, 1981, p 33 IEEE Transactions on Electron Devices, vo. ED-31, No. 8, Aug. 1984, pp 1057, para 4 5; New York, US; S. Miyazawa

DATE CONSIDERED

FORM PTO-1449 U.S. Department of Commerce (Rev. 4/92)

ATTY. DOCKET NO. Patent and Trademark Office 501.22642CC9

SERIAL NO.

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

FUJISAKI

APPLICANT

GROUP

(Use several sheets if necessary)

U.S. PATENT DOCUMENTS

FILING DATE

July 23, 2003

EXAMINER												FILING	DATE	
INITIAL	DOC	DOCUMENT NUMBER							NAME	CLASS			PRIATE	
	4	8	6	3	5	5	4	9/89	Kawasaki	<u> </u>				
	5	7	7	0	8	7	3	6/98	Fujisaki et al		`			
	6	2	9 .	4	8	0	4	9/01	Fujisaki et al	<u> </u>				
		Ì	ļ											
			শ জন্ম		20.82						,			
								 		1		 		
	-	 		-	-		<u> </u>	 				-		
	- ::	├				-	}	 		<u> </u>		-		
Ì	ł	i .	1		1	i	ł ·	ł	ŀ	1 '	ł			
			T	1	Ι	Γ	τ	 	<u></u>		1	YES	NO	
		ļ	<u> </u>		ļ.,	<u> </u>	 	ļ		ļ				
								<u> </u>		<u> </u>				
				<u> </u>				<u> </u>		<u> </u>				
					-									
	- 	†	†		1	1	<u> </u>	<u> </u>		†				
071150		45.17		·		ل			. D		<u> </u>		<u> </u>	
OTHER	JOCUN	<u>IEN I</u>	5 (II	iciuc	ung	Autn	ior, i	itte, Dai	e, Pertinent Pa	ges, E	tc.)			
		Journal of Crystal Growth, Vol. 63 no. 2, Oct. 1983 pp 415-418, Amsterdam NL; Fornari "Dislocation-free silicon-doped gallium arsenide grown by LEC Procedure												
		Terashima "Control of Growth Parameters for Obtaining Highly Uniform Large Diameter LEC GaAs" 5th Conf. On Semi-insulating III-V Materials, 1988 pp 413-422												
		Matsuoko et al "uniformity Evaluation of MESFETs for FGaAs LSI Fabrication" IEEE Trans. On Elec. Dev. Vol ED31, no. 8 Aug. 1984 pp 1062												
		Applied Physics Letters, vol 44, no. 1, Jan. 1984 pp 74-76 New York, US; Hunter "Carbon in Semi-Insulating, liquid Encapsulated Czochralski GaAs"												
		Patent Abstracts of Japan, vol. 4,no. 173 (C-32) [655], 29 Nov. 1980; JP A-55-113-669 Sumitomo 2-09-1980												

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation is considered, draw line through citation if not in conformance and not considered. Include copy of this form with n xt communication to applicant.